

Silicon NPN Power Transistors

2SD1638

DESCRIPTION

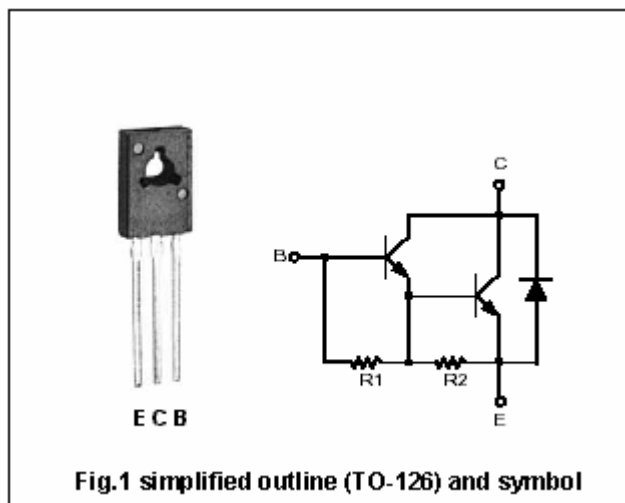
- With TO-126 package
- DARLINGTON

APPLICATIONS

- For low frequency and power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	100	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		2	A
P _D	Total power dissipation	T _C =25°C	10	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA; I _B =0	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1.0A ; I _B =1mA			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1.0A ; I _B =1mA			2.0	V
I _{CEO}	Collector cut-off current	V _{CE} =100V; I _B =0			0.5	mA
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =2V	1000		10000	
C _{OB}	Collector output capacitance	f=0.1MHz ; V _{CB} =10V		25		pF

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PACKAGE OUTLINE

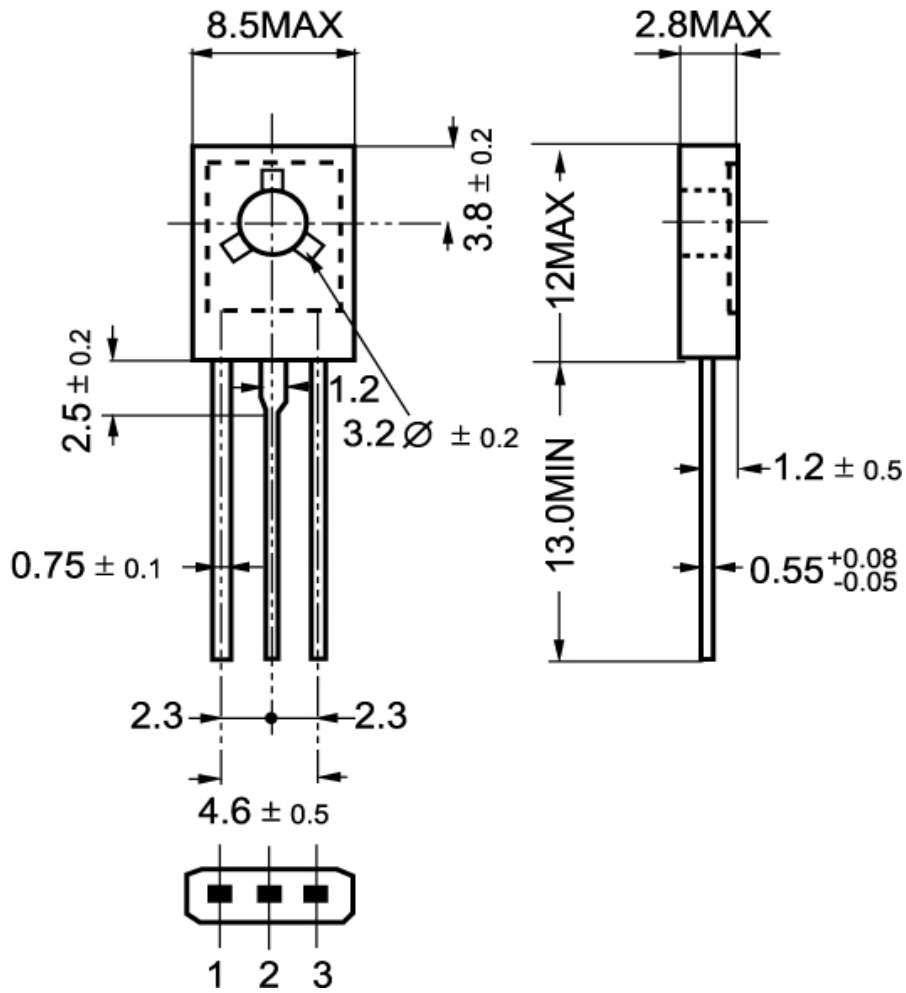


Fig.2 Outline dimensions